Supplementary Page

Thermal Laser Epitaxy of Refractory Metals

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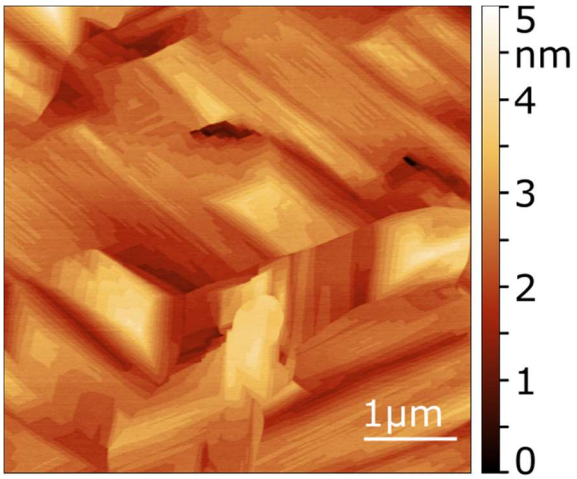

Figure 2 AFM image of a Ta layer grown on c-plane sapphire at 1150 °C (thickness ~ 69 nm).

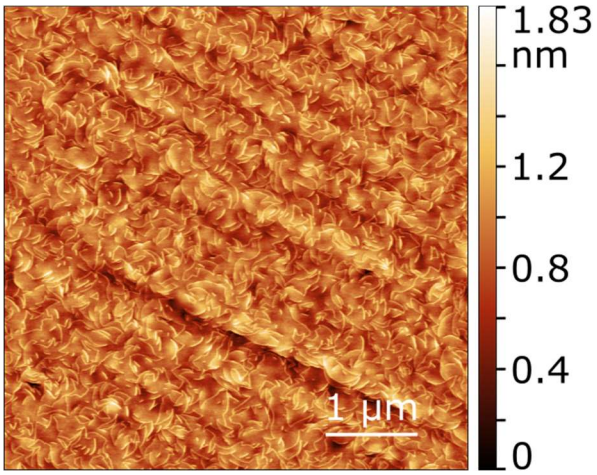

Figure 2 AFM image of a Ru layer grown at room temperature on c-plane sapphire after annealing at 1000 °C (thickness ~ 30 nm).

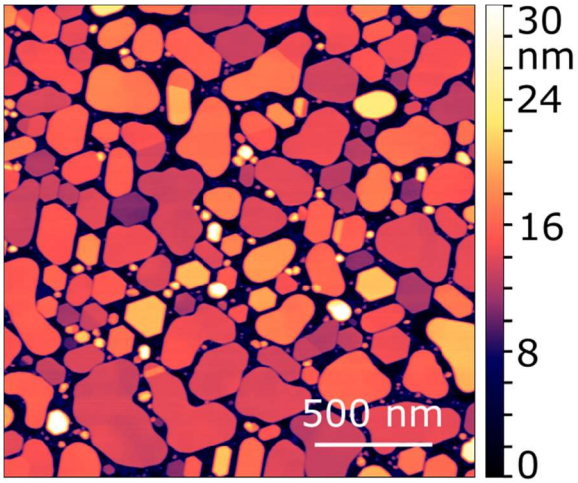

Figure 3 Ru layer grown on a c-plane sapphire substrate heated to a temperature of 1000 °C. Large crystalline islands with flat surfaces are formed.